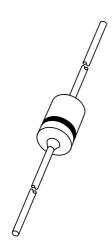
DISCRETE SEMICONDUCTORS

DATA SHEET



1N4148; 1N4448 High-speed diodes

Product data sheet Supersedes data of 2002 Jan 23

2004 Aug 10



High-speed diodes

1N4148; 1N4448

FEATURES

 Hermetically sealed leaded glass SOD27 (DO-35) package

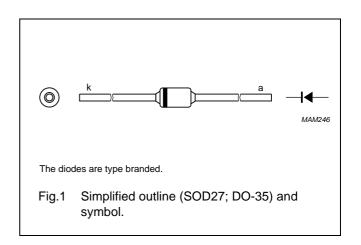
- High switching speed: max. 4 ns
- · General application
- Continuous reverse voltage: max. 100 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA.

APPLICATIONS

· High-speed switching.

DESCRIPTION

The 1N4148 and 1N4448 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD27 (DO-35) packages.



MARKING

| TYPE NUMBER | MARKING CODE |
|-------------|--------------------|
| 1N4148 | 1N4148PH or 4148PH |
| 1N4448 | 1N4448 |

ORDERING INFORMATION

| TYPE NUMBER | PACKAGE NAME DESCRIPTION VERSION | | |
|--------------|-----------------------------------|--|-------|
| TIPE NOWIDER | | | |
| 1N4148 | - | hermetically sealed glass package; axial leaded; 2 leads | SOD27 |
| 1N4448 | | | |

High-speed diodes

1N4148; 1N4448

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|--|------|------|------|
| V _{RRM} | repetitive peak reverse voltage | | _ | 100 | V |
| V _R | continuous reverse voltage | | _ | 100 | V |
| IF | continuous forward current | see Fig.2; note 1 | _ | 200 | mA |
| I _{FRM} | repetitive peak forward current | | _ | 450 | mA |
| I _{FSM} | non-repetitive peak forward current | square wave; $T_j = 25$ °C prior to surge; see Fig.4 | | | |
| | | t = 1 μs | _ | 4 | Α |
| | | t = 1 ms | _ | 1 | Α |
| | | t = 1 s | _ | 0.5 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C; note 1 | _ | 500 | mW |
| T _{stg} | storage temperature | | -65 | +200 | °C |
| Tj | junction temperature | | _ | 200 | °C |

Note

1. Device mounted on an FR4 printed-circuit board; lead length 10 mm.

ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------------|--------------------------|---|------|------|------|
| V _F | forward voltage | see Fig.3 | | | |
| | 1N4148 | I _F = 10 mA | _ | 1 | V |
| | 1N4448 | I _F = 5 mA | 0.62 | 0.72 | V |
| | | I _F = 100 mA | _ | 1 | V |
| I _R | reverse current | V _R = 20 V; see Fig.5 | | 25 | nA |
| | | $V_R = 20 \text{ V}; T_j = 150 ^{\circ}\text{C}; \text{ see Fig.5}$ | _ | 50 | μΑ |
| I _R | reverse current; 1N4448 | $V_R = 20 \text{ V}; T_j = 100 ^{\circ}\text{C}; \text{ see Fig.5}$ | _ | 3 | μΑ |
| C _d | diode capacitance | f = 1 MHz; V _R = 0 V; see Fig.6 | _ | 4 | pF |
| t _{rr} | reverse recovery time | when switched from I_F = 10 mA to I_R = 60 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7 | _ | 4 | ns |
| V _{fr} | forward recovery voltage | when switched from $I_F = 50$ mA; $t_r = 20$ ns; see Fig.8 | - | 2.5 | V |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|-----------------------|---|---------------------------|-------|------|
| R _{th(j-tp)} | thermal resistance from junction to tie-point | lead length 10 mm | 240 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | lead length 10 mm; note 1 | 350 | K/W |

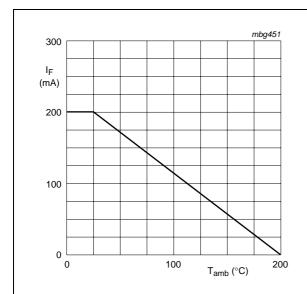
Note

1. Device mounted on a printed-circuit board without metallization pad.

High-speed diodes

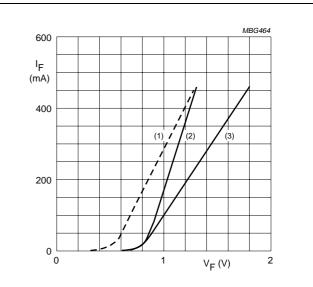
1N4148; 1N4448

GRAPHICAL DATA



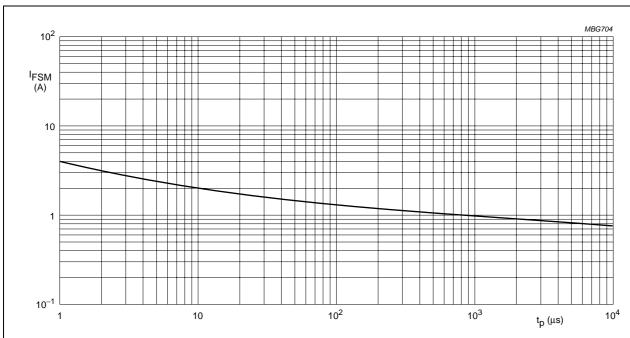
Device mounted on an FR4 printed-circuit board; lead length 10 mm.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 175 \,^{\circ}\text{C}$; typical values.
- (2) $T_j = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



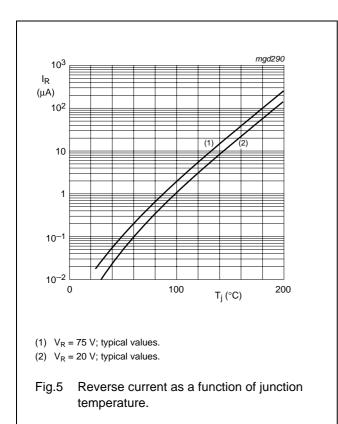
Based on square wave currents.

 $T_j = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

High-speed diodes

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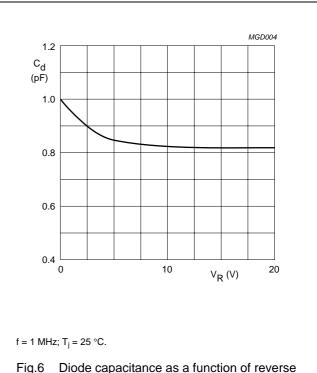
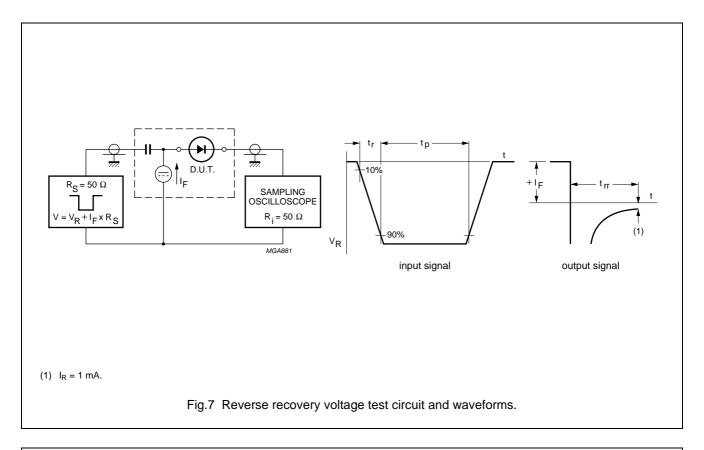
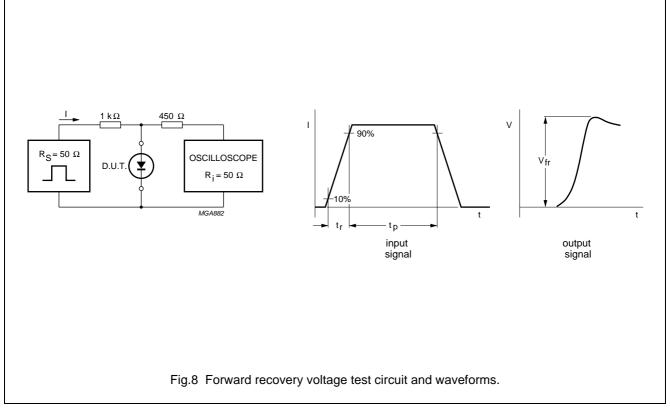


Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed diodes

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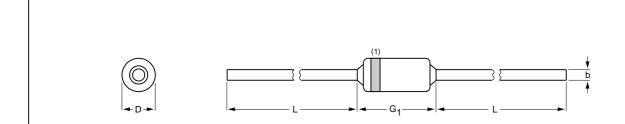
High-speed diodes

1N4148; 1N4448

PACKAGE OUTLINE

Hermetically sealed glass package; axial leaded; 2 leads

SOD27



DIMENSIONS (mm are the original dimensions)

| UNIT | b | D | G ₁ | L |
|------|------|------|----------------|------|
| | max. | max. | max. | min. |
| mm | 0.56 | 1.85 | 4.25 | 25.4 |

0 1 2 mm scale

Note

1. The marking band indicates the cathode.

| OUTLINE | REFERENCES | | EUROPEAN | ISSUE DATE | | |
|---------|------------|-------|----------|------------|-----------------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA | | PROJECTION ISSUE DATE | |
| SOD27 | A24 | DO-35 | SC-40 | | | 97-06-09 05-12-22 |

High-speed diodes

1N4148; 1N4448

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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